Effects of the Ar pressure on the magnetic and magnetocaloric properties of sputtered Er-Co thin films

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Due to its eco-friendly characteristics and high cooling efficiency, the magnetic refrigeration utilizing the magnetocaloric effect has attracted a lot of research interests.^{1,2} This study deals with the change in the magnetic and magnetoclaoric properties of Er-Co thin films as a function of the Ar pressure during sputtering. The thin films with the structure of Ta/Er-Co/Ta were fabricated on a Si/SiO₂ substrate by using a DC magnetron sputtering system. The sputtering conditions were fixed, except for the Ar pressure which was varied widely from 2 to 10 mTorr in steps of 2 mTorr. The amount of Co, relative to Er, decreases with increasing Ar pressure and the

specific compositions are as follows: ErCo_{1.07}, ErCo_{1.04}, ErCo_{1.00}, ErCo_{0.96}, ErCo_{0.93}. All the samples show a good magnetic softness, which can be expected from the amorphous phase in the as-deposited state. The magnetization-temperature curves indicate a typical ferrimangetic behavior, with the compensation temperature ranging from 83 to 185 K. Considering a small change in composition, this large change in the compensation temperature is unexpected. One possibility can be a large difference in the amorphous structure (such as short-range ordering) depending on the Ar pressure. The results for the temperature dependence of $-\Delta S_M$ (magnetic entropy change) are shown in Fig. 1. A broad maximum is observed in all the samples. Both the maximum temperature and the absolute value of ΔS_M increase monotonically with increasing Ar pressure.

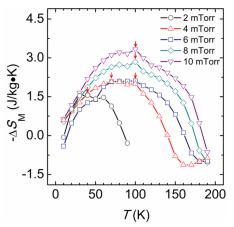


Fig. 1. Temperature dependence of $-\Delta S_{\rm M}$ under a magnetic field change of 70 kOe for the samples fabricated at different Ar pressures during sputtering.

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References

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